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(54) **HIGH DENSITY TRENCH FET WITH INTEGRATED SCHOTTKY DIODE AND METHOD OF MANUFACTURE**

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H01L 29/76 (2006.01)
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(74) *Attorney, Agent, or Firm*—Townsend and Townsend and Crew LLP

(52) **U.S. Cl.** **257/330**; 257/328; 257/329;
257/409; 257/E21.418; 257/E21.419

(57) **ABSTRACT**

(58) **Field of Classification Search** 257/328,
257/330, 331
See application file for complete search history.

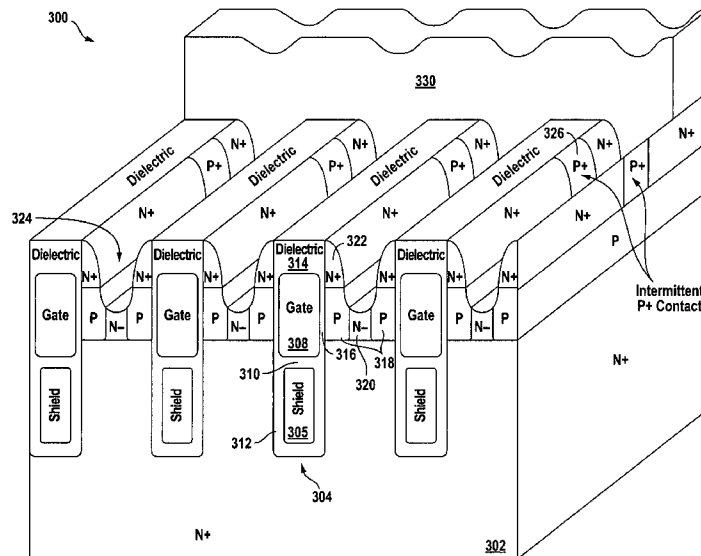
A monolithically integrated trench FET and Schottky diode includes a pair of trenches terminating in a first silicon region of first conductivity type. Two body regions of a second conductivity type separated by a second silicon region of the first conductivity type are located between the pair of trenches. A source region of the first conductivity type is located over each body region. A contact opening extends between the pair of trenches to a depth below the source regions. An interconnect layer fills the contact opening so as to electrically contact the source regions and the second silicon region. Where the interconnect layer electrically contacts the second silicon region, a Schottky contact is formed.

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28 Claims, 7 Drawing Sheets



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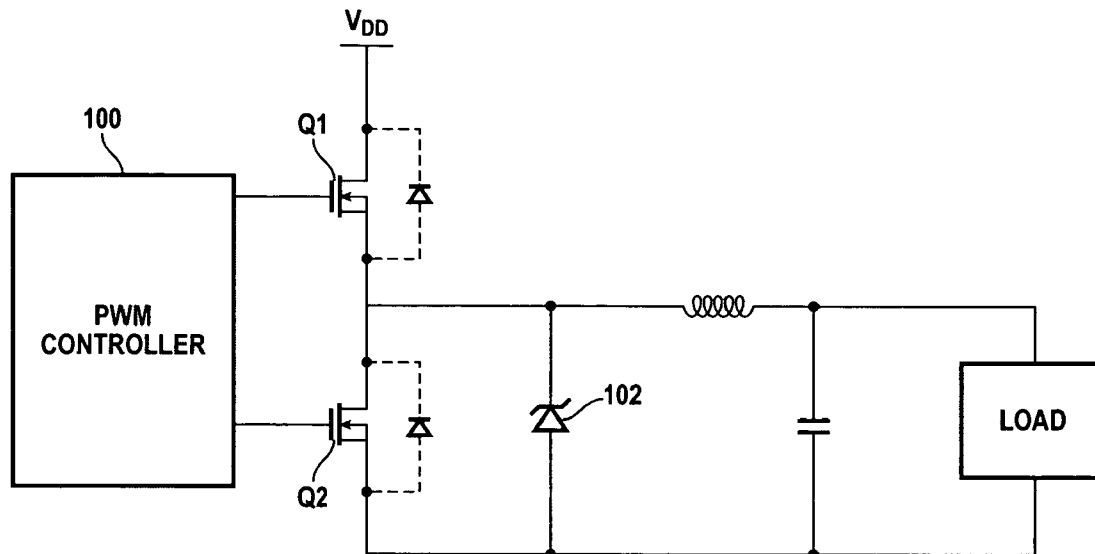


FIG. 1
(PRIOR ART)

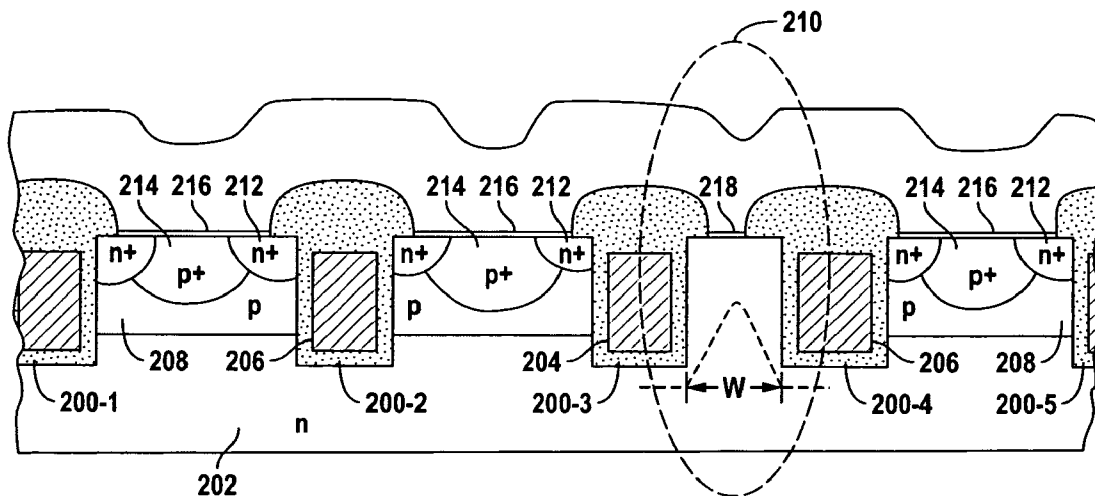


FIG. 2
(PRIOR ART)

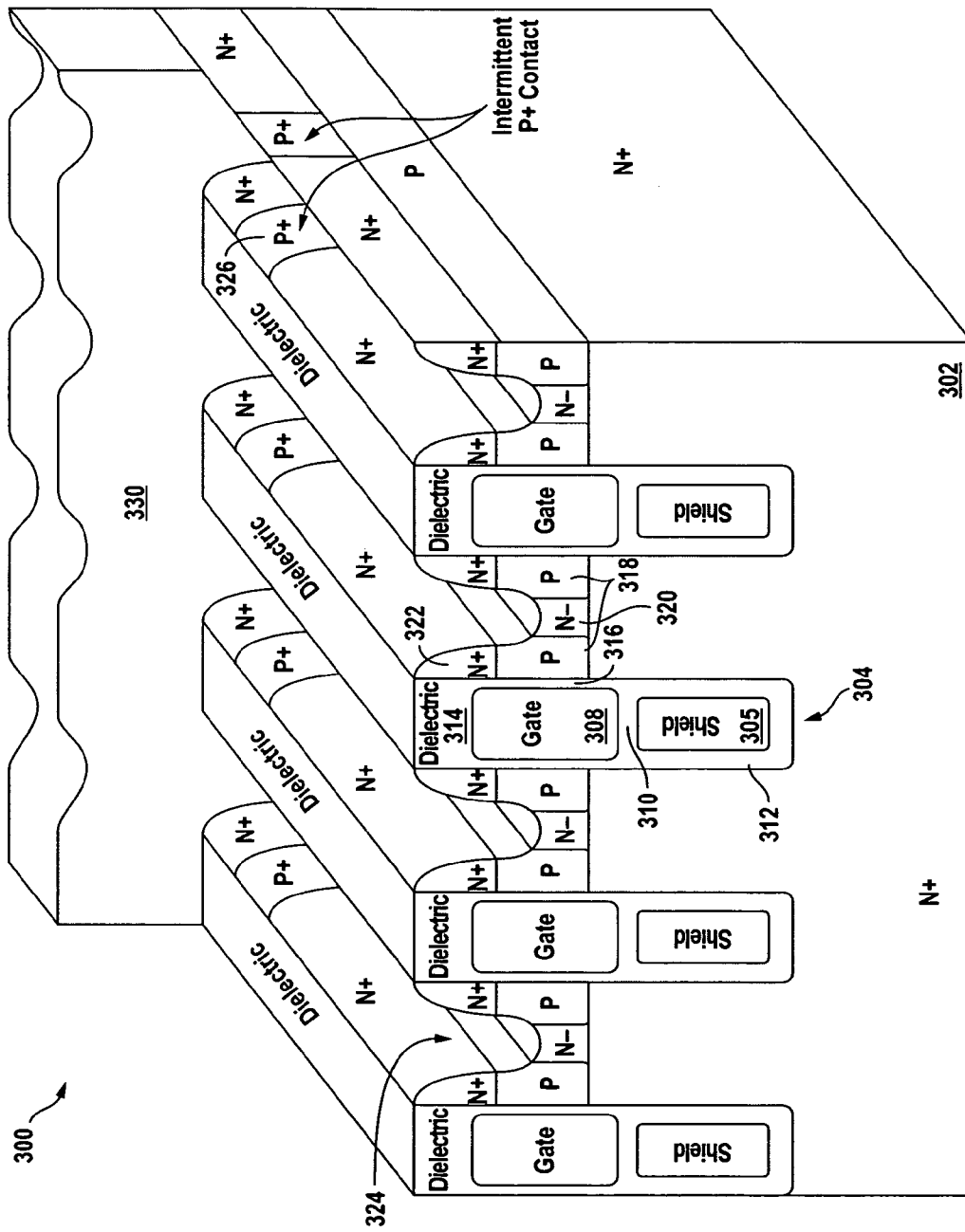


FIG. 3

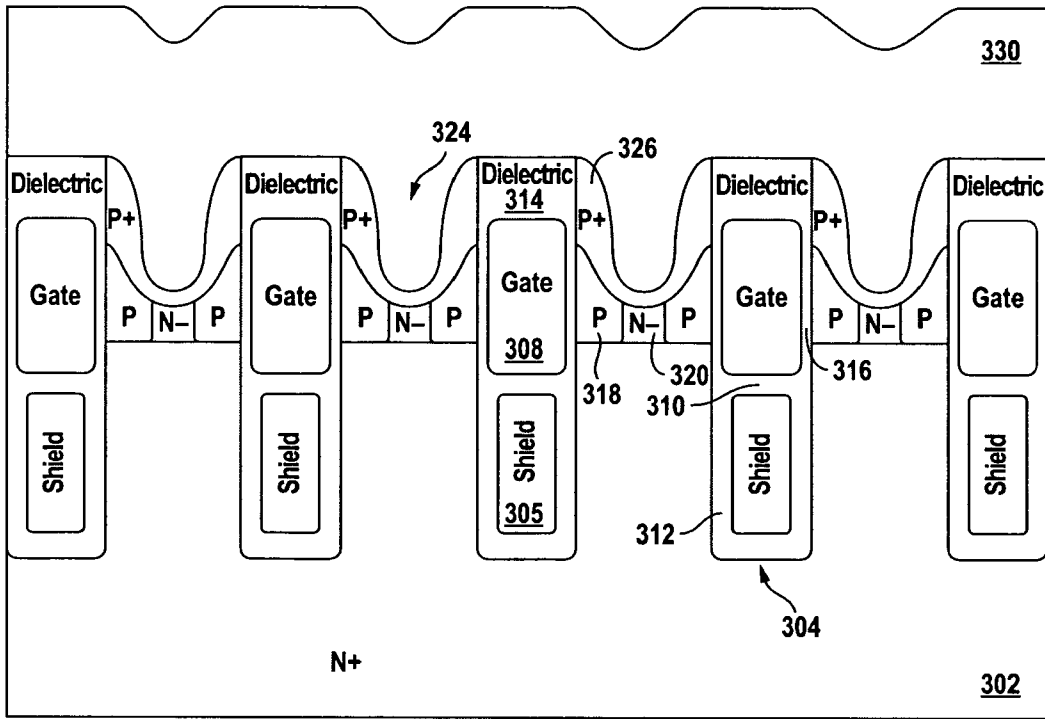


FIG. 4

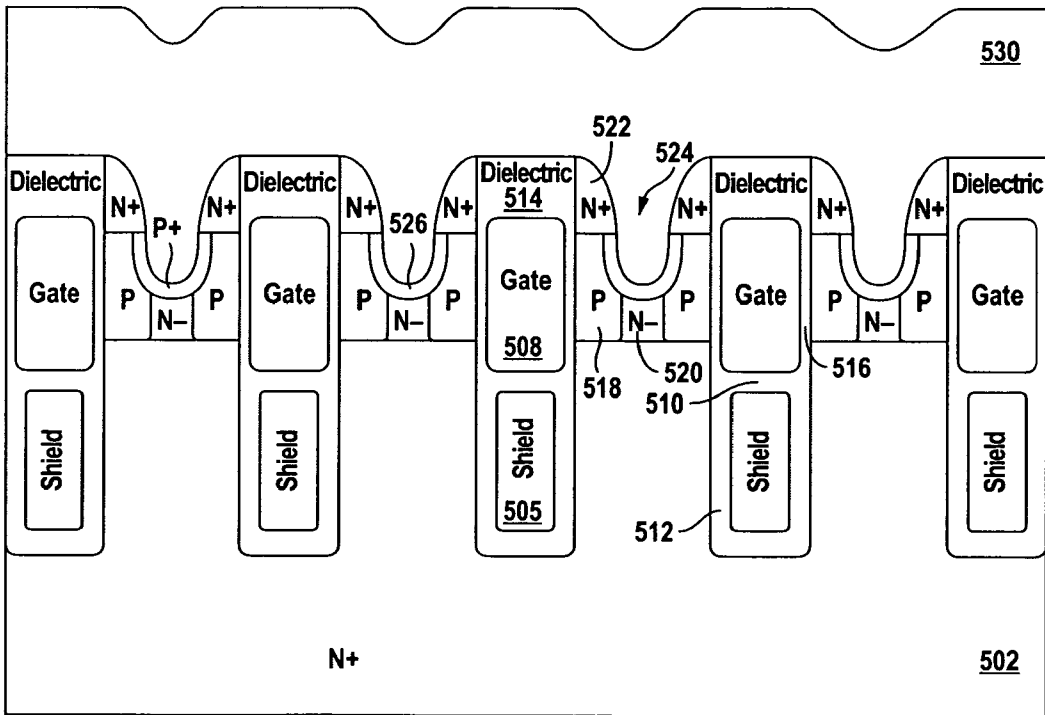


FIG. 5

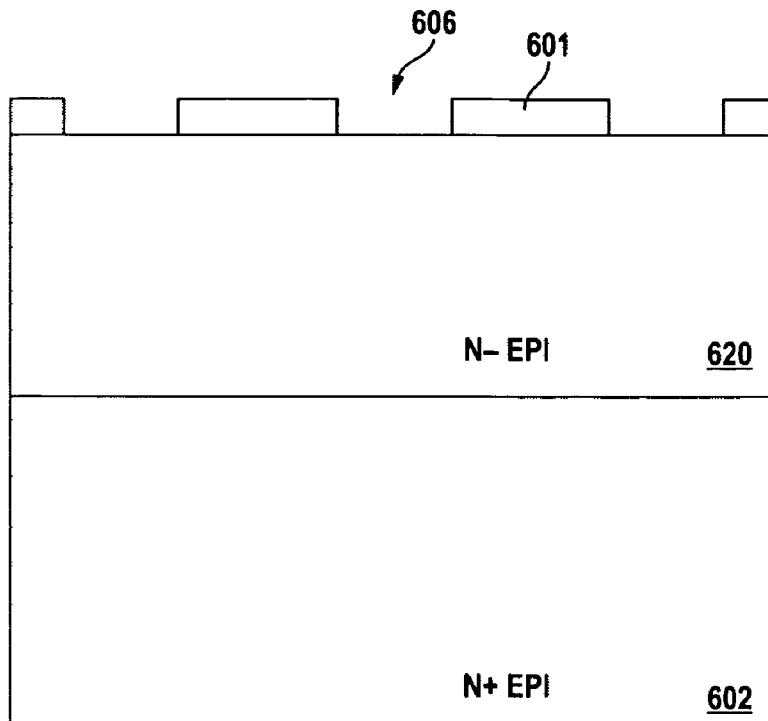


FIG. 6A

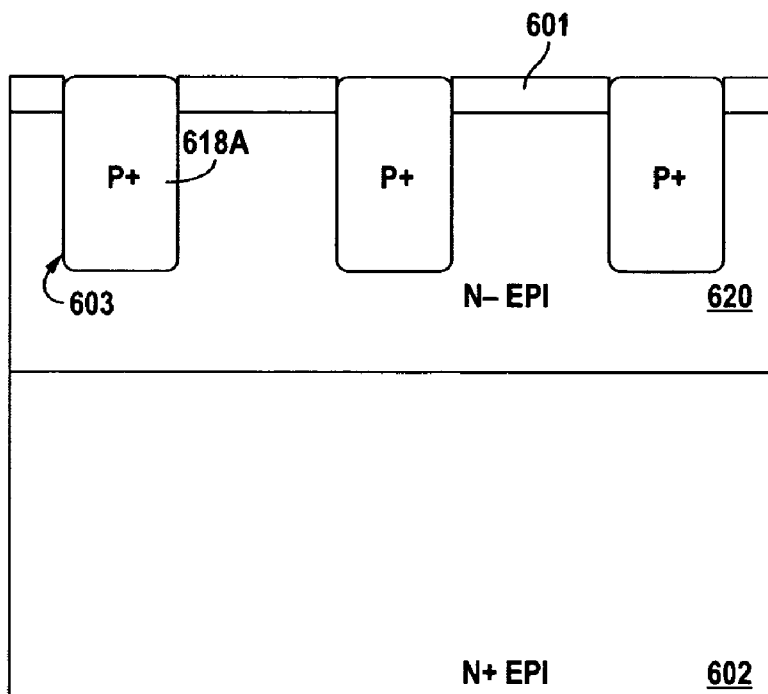


FIG. 6B

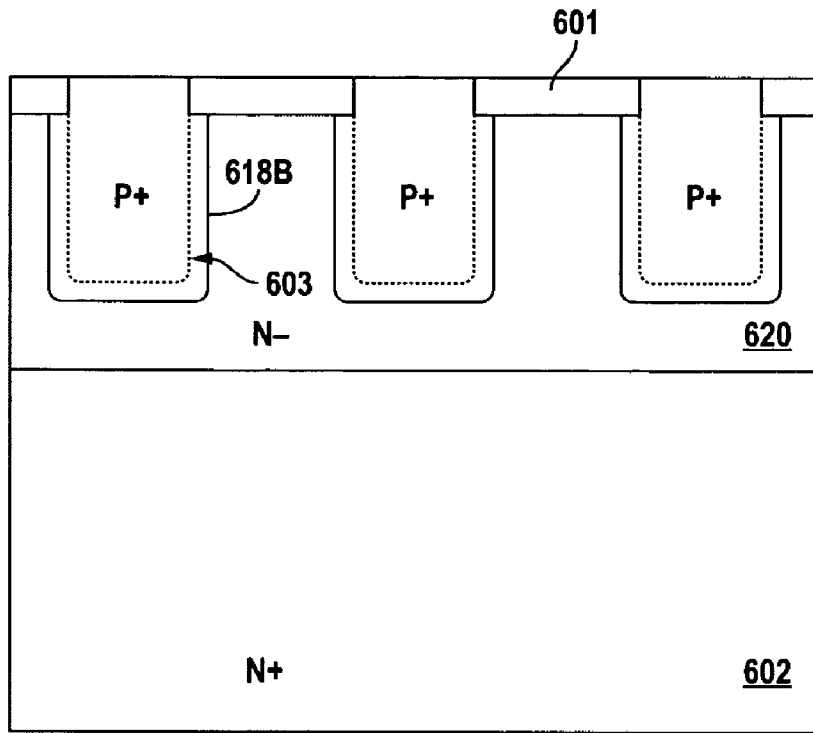


FIG. 6C

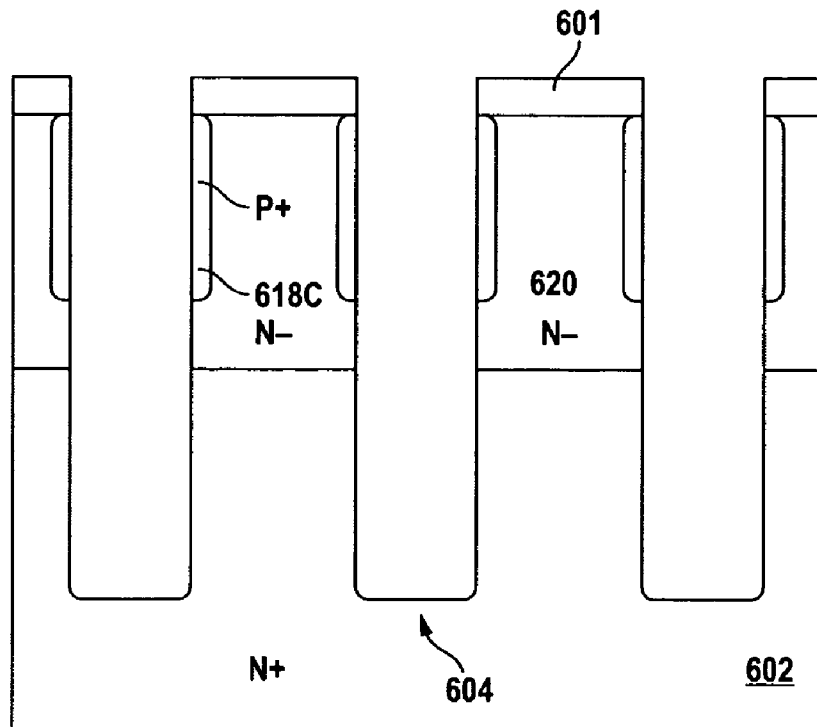


FIG. 6D

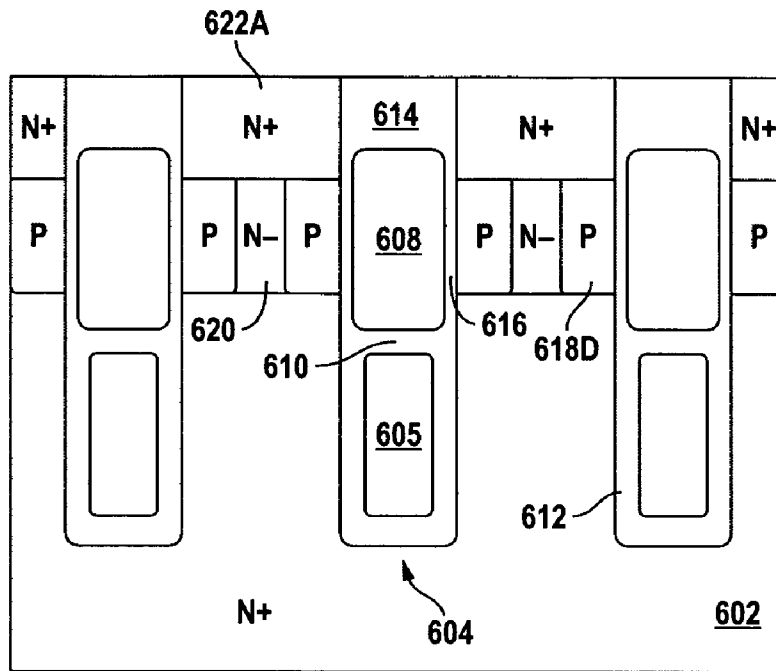


FIG. 6E

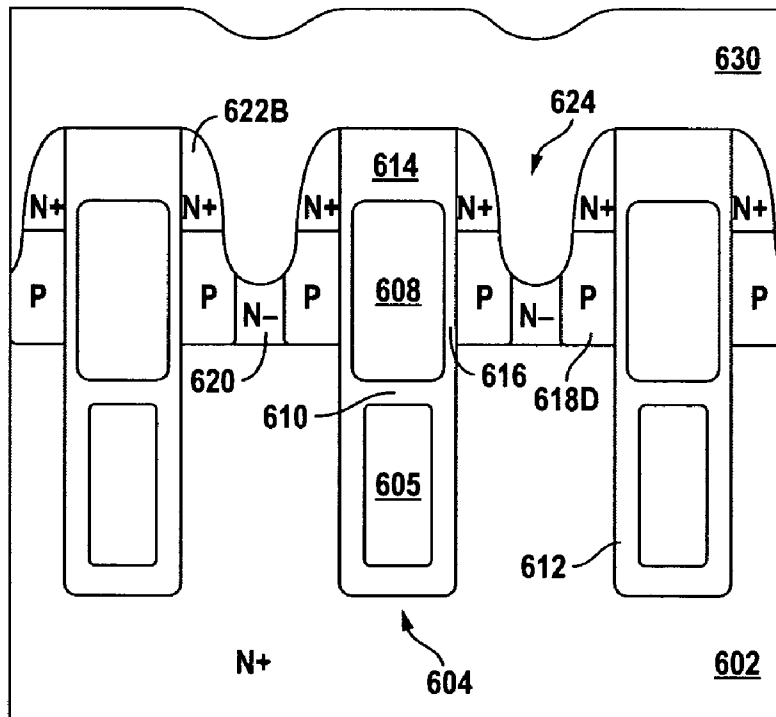


FIG. 6F

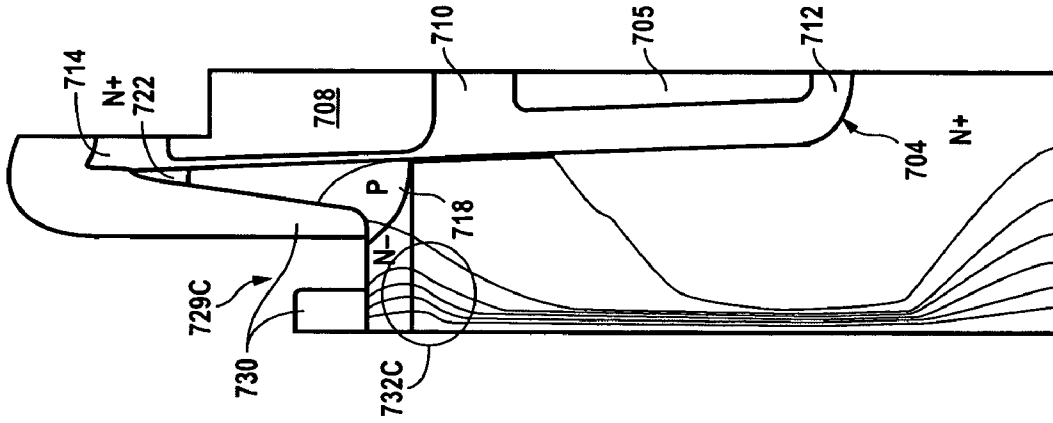


FIG. 7C

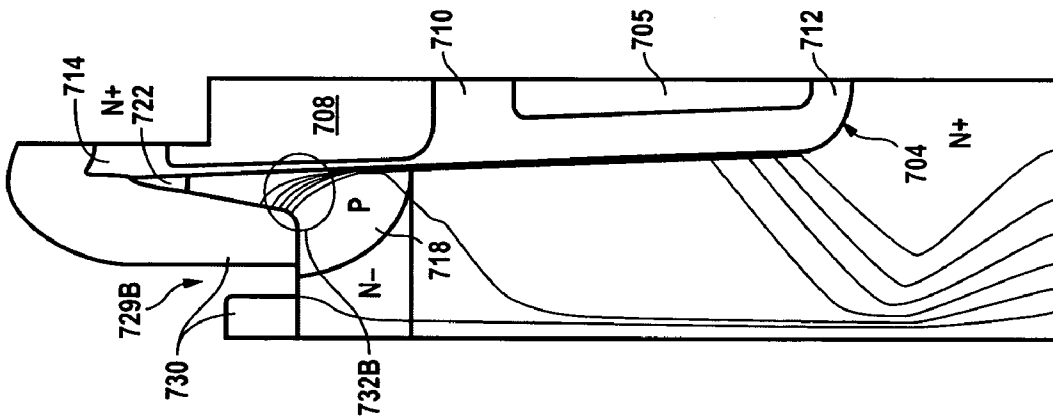


FIG. 7B

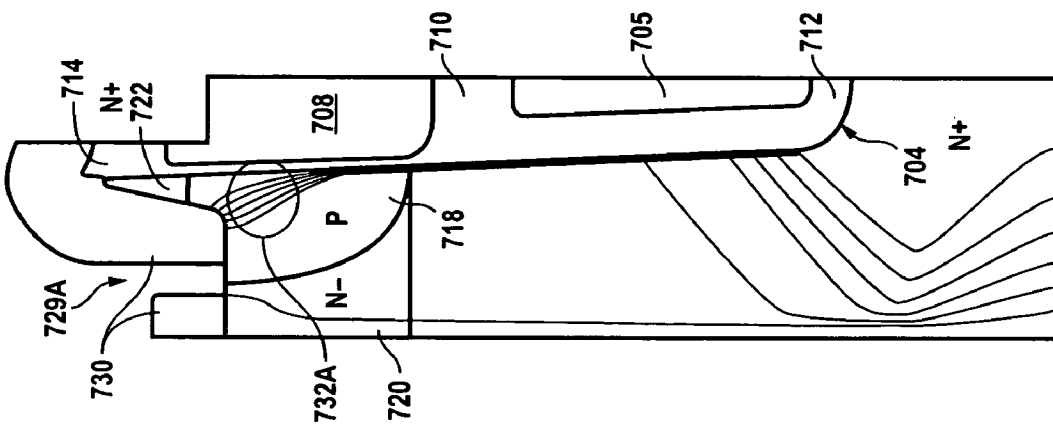


FIG. 7A

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HIGH DENSITY TRENCH FET WITH INTEGRATED SCHOTTKY DIODE AND METHOD OF MANUFACTURE

CROSS-REFERENCES TO RELATED APPLICATIONS

This application is related to the commonly assigned U.S. application Ser. No. 11/026,276, filed Dec. 29, 2004, which disclosure is incorporated herein by reference in its entirety for all purposes.

BACKGROUND OF THE INVENTION

The present invention relates in general to semiconductor power device technology, and in particular to structures and methods for forming a monolithically integrated trench gate field effect transistor (FET) and Schottky diode.

In today's electronic devices it is common to find the use of multiple power supply ranges. For example, in some applications, central processing units are designed to operate with a different supply voltage at a particular time depending on the computing load. Consequently, dc/dc converters have proliferated in electronics to satisfy the wide ranging power supply needs of the circuitry. Common dc/dc converters utilize high efficiency switches typically implemented by power MOSFETs. The power switch is controlled to deliver regulated quanta of energy to the load using, for example, a pulse width modulated (PWM) methodology.

FIG. 1 shows a circuit schematic for a conventional dc/dc converter. A PWM controller **100** drives the gate terminals of a pair of power MOSFETs **Q1** and **Q2** to regulate the delivery of charge to the load. MOSFET switch **Q2** is used in the circuit as a synchronous rectifier. In order to avoid shoot-through current, both switches must be off simultaneously before one of them is turned on. During this "dead time," the internal diode of each MOSFET switch, commonly referred to as body diode, can conduct current. Unfortunately the body diode has relatively high forward voltage and energy is wasted. To improve the conversion efficiency of the circuit, a Schottky diode **102** is often externally added in parallel with the MOSFET (**Q2**) body diode. Because a Schottky diode has lower forward voltage than the body diode, Schottky diode **102** effectively replaces the MOSFET body diode. The lower forward voltage of the Schottky diode results in improved power consumption.

For many years, the Schottky diode was implemented external to the MOSFET switch package. More recently, some manufacturers have introduced products in which discrete Schottky diodes are co-packaged with discrete power MOSFET devices. There have also been monolithic implementations of power MOSFETs with Schottky diode. An example of a conventional monolithically integrated trench MOSFET and Schottky diode is shown in FIG. 2. A Schottky diode **210** is formed between two trenches **200-3** and **200-4** surrounded by trench MOSFET cells on either side. N-type substrate **202** forms the cathode terminal of Schottky diode **210** as well as the drain terminal of the trench MOSFET. Conductive layer **218** provides the diode anode terminal and also serves as the source interconnect layer for MOSFET cells. The gate electrode in trenches **200-1**, **200-2**, **200-3**, **200-4** and **200-5** are connected together in a third dimension and are therefore similarly driven. The trench MOSFET cells further include body regions **208** with source region **212** and heavy body regions **214** therein.

The Schottky diodes in FIG. 2 are interspersed between trench MOSFET cells. As a result, the Schottky diodes con-

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sume a significant portion of the active area, resulting in lower current ratings or a large die size. There is therefore a need for a monolithically and densely integrated Schottky diode and trench gate FET with superior performance characteristics.

BRIEF SUMMARY OF THE INVENTION

In accordance with an embodiment of the invention, a monolithically integrated trench FET and Schottky diode includes a pair of trenches terminating in a first silicon region of first conductivity type. Two body regions of a second conductivity type separated by a second silicon region of the first conductivity type are located between the pair of trenches. A source region of the first conductivity type is located over each body region. A contact opening extends between the pair of trenches to a depth below the source regions. An interconnect layer fills the contact opening so as to electrically contact the source regions and the second silicon region. Where the interconnect layer electrically contacts the second silicon region, a Schottky contact is formed.

In one embodiment, the first silicon region has a higher doping concentration than the second silicon region.

In another embodiment, each body region vertically extends between a corresponding source region and the first silicon region, and the interconnect layer electrically contacts the second silicon region at a depth along the bottom half of the body regions.

In another embodiment, each of the two body regions has a substantially uniform doping concentration.

In another embodiment, a heavy body region of the second conductivity type is formed between the pair of trenches such that the heavy body region electrically contacts each of the two body regions and the second silicon region.

In another embodiment, the two body regions, the source regions, and the heavy body region are self-aligned to the pair of trenches.

In another embodiment, the two body regions and the second silicon region have substantially the same depth.

In accordance with another embodiment of the invention, a monolithically integrated trench FET and Schottky diode is formed as follows. Two trenches are formed extending through an upper silicon layer and terminating within a lower silicon layer. The upper and lower silicon layers have a first conductivity type, and the upper silicon layer extends over the lower silicon layer. First and second silicon regions of a second conductivity type are formed in the upper silicon layer between the pair of trenches. A third silicon region of the first conductivity type is formed extending into the first and second silicon regions between the pair of trenches such that remaining lower portions of the first and second silicon regions form two body regions separated by a portion of the upper silicon layer. A silicon etch is performed to form a contact opening extending through the first silicon region such that outer portions of the first silicon region remain. The outer portions of the first silicon region form source regions. An interconnect layer is formed filling the contact opening so as to electrically contact the source regions and the portion of the upper silicon layer. Where the interconnect layer electrically contacts the second silicon region, a Schottky contact is formed.

In one embodiment, the lower silicon layer has a higher doping concentration than the upper silicon layer.

In another embodiment, the electrical contact between the interconnect layer and the portion of the upper silicon layer is made at a depth below the source regions.

In another embodiment, each of the first and second regions has a substantially uniform doping concentration.

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In another embodiment, a heavy body region of the second conductivity type is formed between the pair of trenches. The heavy body region extends into the two body regions and into the portion of the upper silicon layer.

In yet another embodiment, the two body regions, the source regions, and the heavy body region are self-aligned to the pair of trenches.

A further understanding of the nature and the advantages of the invention disclosed herein may be realized by reference to the remaining portions of the specification and the attached drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a circuit schematic for a conventional dc/dc converter using power MOSFETs with a Schottky diode;

FIG. 2 shows a cross-sectional view of a conventional monolithically integrated trench MOSFET and Schottky diode;

FIG. 3 is an exemplary simplified isometric view of a portion of an array of stripe-shaped cells each having a trench MOSFET and a Schottky diode integrated therein, in accordance with an embodiment of the invention;

FIG. 4 shows a cross-section view along heavy body regions 326 in FIG. 3;

FIG. 5 is a simplified cross section view showing an alternate implementation of the heavy body region to that shown in FIGS. 3 and 4, in accordance with an embodiment of the invention;

FIGS. 6A-6F are simplified cross section views illustrating an exemplary process sequence for forming the monolithically integrated trench MOSFET and Schottky diode shown in FIG. 3, according to an embodiment of the present invention; and

FIGS. 7A-7C show simulated avalanche current flow lines for three different dimple depths in a monolithically integrated trench MOSFET and Schottky diode structure.

DETAILED DESCRIPTION OF THE INVENTION

In accordance with embodiments of the invention, a Schottky diode is optimally integrated with a trench MOSFET in a single cell repeated many times in an array of such cells. Minimal to no active area is sacrificed in integrating the Schottky diode, yet the total Schottky diode area is large enough to handle 100% of the diode forward conduction. The MOSFET body diode thus never turns on, eliminating reverse recovery losses. Further, because of Schottky diode's lower forward voltage drop compared to that of the MOSFET body diode, power losses are reduced.

Moreover, the Schottky diode is integrated with the MOSFET such that the Schottky contact is formed below the MOSFET source regions. This advantageously diverts the avalanche current away from the source regions toward the Schottky regions, preventing the parasitic bipolar transistor from turning on. The device ruggedness is thus improved. This feature of the invention also eliminates, for the most part, the need for heavy body regions typically required in each MOSFET cell of prior art structures to prevent the parasitic bipolar transistor from turning on. Instead, islands of heavy body regions are incorporated intermittently and far apart from one another merely to ensure good source metal to body region contact. In essence, the heavy body regions required in prior art trench MOSFETs are, for the most part, replaced with Schottky diode. Accordingly, no additional silicon area is allocated to the Schottky diode.

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FIG. 3 is an exemplary simplified isometric view of a portion of an array of stripe-shaped cells each having a trench MOSFET and a Schottky diode integrated therein, in accordance with an embodiment of the invention. A highly doped N-type (N+) region 302 overlies an N-type silicon substrate (not shown) which has an even higher doping concentration (N++) than N+ region 302. A plurality of trenches 304 extend to a predetermined depth within N+ region 302. A shield electrode 305 and an overlying gate electrode 308 are embedded in each trench 304. In one embodiment, shield electrodes 305 and gate electrodes 308 comprise polysilicon. An inter-electrode dielectric 310 insulates the gate and shield electrodes from one another. Shield dielectric layer 312 lines lower sidewalls and bottom of each trench 304, and insulates shield electrodes 305 from surrounding N+ region 302. A gate dielectric 316, which is thinner than shield dielectric 312, lines the upper sidewalls of trenches 304. A dielectric cap 314 extends over each gate electrode 308. In one embodiment, shield electrodes 305 are electrically connected to source regions along a third dimension, and thus are biased to the same potential as the source regions during operation. In other embodiments, shield electrodes 305 are electrically tied to gate electrodes 308 along a third dimension, or are allowed to float.

Two P-type body regions 318 separated by a lightly doped N-type (N-) region 320 are located between every two adjacent trenches 304. Each body region 318 extends along one trench sidewall. In the various embodiments shown in the figures and described herein, body regions 318 and N- region 320 have substantially the same depth, however body regions 318 may be slightly shallower or deeper than N- region 320 and vice versa without any significant impact on the device operation. A highly doped N-type source region 322 is located directly above each body region 318. Source regions 322 vertically overlap gate electrode 308, and possess a rounded outer profile due to the presence of dimples 324 forming contact openings. Each dimple 324 extends below corresponding source regions 322 between every two adjacent trenches. As shown, source regions 322 and body regions 318 together form the rounded sidewalls of dimples 324, and N- regions 320 extend along the bottom of dimples 324. In one embodiment, N+ region 302 is an N+ epitaxial layer, and N- regions 320 are portions of an N- epitaxial layer in which body regions 318 and source regions 322 are formed. When MOSFET 300 is turned on, a vertical channel is formed in each body region 318 between each source region 322 and the highly doped region 302 along trench sidewalls.

A Schottky barrier metal 330, which is peeled back in FIG. 3 to expose the underlying regions, fills dimples 324 and extends over dielectric caps 314. Schottky barrier metal 330 electrically contacts N- regions 320 along the bottom of dimples 324, thus forming a Schottky contact. Schottky barrier metal 330 also serves as the top-side source interconnect, electrically contacting source regions 322 and heavy body regions 326.

During reverse bias, the depletion regions formed at each body/N- junction advantageously merge in N- region 320 thus fully depleting N- region 320 beneath the Schottky contact. This eliminates the Schottky leakage current which in turn allows the use of barrier metals with lower work functions. An even lower forward voltage is thus obtained for the Schottky diode.

Islands of heavy body regions 326 are formed intermittently along the cell stripes, as shown. Heavy body regions 326 extend through N- regions 320. This is more clearly shown in FIG. 4 which is a cross-section view through heavy body regions 326 of the structure in FIG. 3. The cross section

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view in FIG. 4 is, for the most part, similar to the cross section view along the face of the isometric view in FIG. 3 except that in FIG. 4 the two source regions between every two adjacent trenches are replaced with one contiguous heavy body region 326 extending through N- regions 320. Heavy body regions 326 provide ohmic contact between source metal 330 and body regions 318. Because heavy body regions 326 extend through N- regions 320, no Schottky diode is formed in these regions. No MOSFET current flows in these regions either, because of the absence of source regions.

FIG. 5 is a simplified cross section view showing an alternate implementation of the heavy body region to that in FIGS. 3 and 4, in accordance with another embodiment of the invention. In FIG. 5, heavy body regions 526 extend only along a bottom portion of each dimple 524 such that source regions 522 are kept intact. Thus, MOSFET current does flow in these regions, but heavy body regions 526 prevent Schottky barrier metal 530 from contacting N-regions 310 and thus no Schottky diode is formed in these regions.

Referring back to FIG. 3, the intermittent placing of heavy body regions 326 differs from conventional implementations where heavy body regions extend along the entire length of the cell stripes between two adjacent source regions as in the prior art FIG. 2 structure. Continuous heavy body regions are not needed in the FIG. 3 structure because of the manner in which the Schottky diode is integrated with the trench MOSFET. As can be seen in FIG. 3, by extending dimples 324 well below source regions 322, the Schottky contacts are similarly formed well below source regions 322. As described more fully in connection with FIGS. 7A-7C below, with the Schottky contacts positioned well below source regions 322, the avalanche current is diverted away from source regions 322 toward the Schottky regions, thus preventing the parasitic bipolar transistor from turning on. This eliminates the need for continuous heavy body regions along the cell stripes typically required in prior art structures. Instead, islands of heavy body regions 326 are incorporated intermittently and far apart from one other along the cell stripes to ensure good source metal 330 to body region 318 contact. With the continuous heavy body regions replaced, for the most part, with Schottky regions, no additional silicon area needs to be allocated to the Schottky diode. Thus no silicon area is sacrificed in integrating the Schottky diode.

In some embodiments, the placement frequency of heavy body regions 326 along the stripes is dictated by the device switching requirements. For faster switching devices, heavy body regions are placed more frequently along the stripes. For these devices, additional silicon area may need to be allocated to Schottky diode (e.g., by increasing the cell pitch). For slower switching devices, fewer heavy body regions are required along the stripes. For these devices, placing a heavy body region at each end of a stripe may suffice, thus maximizing the Schottky diode area.

FIGS. 6A-6F are simplified cross section views illustrating an exemplary process sequence for forming the integrated MOSFET-Schottky structure in FIG. 3, according to an embodiment of the present invention. In FIG. 6A, two epitaxial layers 602 and 620 overlying a silicon substrate (not shown) are formed using conventional techniques. Epitaxial layer 620 which is a lightly doped N-type layer (N-) extends over epitaxial layer 620 which is a highly doped N-type layer (N+). A hard mask (e.g., comprising oxide) is formed, patterned and etched to form hard mask islands 601 over N- epi 620. Surface areas of the N- epi 620 are thus exposed through openings 606 defined by hard mask islands 601. In one embodiment, openings 606, which define the trench width, are about 0.3 μm each, and the width of each hard mask island

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601 is in the range of 0.4-0.8 μm . These dimensions define the cell pitch within which the MOSFET and Schottky diode are formed. Factors impacting these dimensions include the capabilities of the photolithographic equipment and the design and performance goals.

In FIG. 6B, trenches 603 terminating within N- epi 620 are formed by etching silicon through openings 606 using conventional silicon etch techniques. In one embodiment, trenches 603 have a depth of about 1 μm . A conventional selective epitaxial growth (SEG) process is then used to grow highly doped P-type (P+) silicon regions 618A within each trench 603. In one embodiment, P+ silicon region 618A has a doping concentration of about $5 \times 10^{17} \text{ cm}^{-3}$. In another embodiment, prior to forming P+ regions 618, a thin layer of high-quality silicon lining the sidewalls and bottom of trenches 608 is formed. The thin silicon layer serves as an undamaged silicon surface suitable for growth of the P+ silicon.

In FIG. 6C, a diffusion process is performed to diffuse the p-type dopants into P+ region 618A into N- epi 620. Out-diffused P+ regions 618B extending laterally under hard mask islands 601 and downward into N- epi 620 are thus formed. Multiple thermal cycles may be carried out to achieve the desired out-diffusion. The dotted lines in FIG. 6C show the outline of trenches 603. This diffusion process, as well as other thermal cycles in the process, causes N+ epi 602 to diffuse upward. These upward diffusions of N+ epi 602 need to be accounted for in selecting the thickness of N- epi 620.

In FIG. 6D, using hard mask islands 601, a deep trench etch process is performed to form trenches 604 extending through P+ regions 618B and N- epi 620, terminating in N+ epi 602. In one embodiment, trenches 604 have a depth of about 2 μm . The trench etch process cuts through and removes a central portion of each P+ silicon region 618B, leaving vertically outer P+ strips 618C extending along trench sidewalls.

In another embodiment of the invention, P+ strips 618C are formed using a two-pass angled implant instead of the SEG technique depicted by FIGS. 6B-6D, as described next. In FIG. 6B, after forming trenches 603 through mask openings 606, P-type dopants such as boron are implanted into opposing trench sidewalls using conventional two-pass angled implant techniques. Hard mask islands 604 serve as blocking structures during the implantation process to prevent the implant ions from entering the mesa regions and to confine the location of the implanted ions to the desired regions in N- epi 620. To arrive at the structure shown in FIG. 6D, after the two pass angled implant, a second trench etch is carried out to extend the depth of trenches 603 into N+ epi 602. In an alternate variation, only one trench etch (rather than two) is performed as follows. In FIG. 6B, using hard mask islands 601, a trench etch is carried out to form trenches extending into N+ epi 602 to about the same depth as trenches 604 in FIG. 6D. A two-pass angled implant is then carried out to implant P-type dopants into opposing trench sidewalls. The implant angle and the thickness of hard mask islands 601 are adjusted to define upper trench sidewall regions that are to receive the implant ions.

In FIG. 6E, a shielded gate structure is formed in trenches 604 using known techniques. A shield dielectric 612 lining lower sidewalls and bottom of trenches 604 is formed. Shield electrodes 605 are then formed filling a lower portion of trenches 604. An inter-electrode dielectric layer 610 is then formed over shield electrode 605. A gate dielectric 616 lining upper trench sidewalls is then formed. In one embodiment, gate dielectric 616 is formed in an earlier stage of the process. Recessed gate electrodes 608 are formed filling an upper

portion of trenches **604**. Dielectric cap regions **614** extend over gate electrodes **608** and fill the remainder of trenches **604**.

Next, N-type dopants are implanted into all exposed silicon regions followed by a drive in process, thereby forming N+ regions **622A**. No mask is used in the active region in forming N+ regions **622A**. As shown in FIG. 6E, the various thermal cycles associated with forming the shielded gate structure and the N+ regions **622A** cause P-type regions **618C** to out-diffuse thereby forming wider and taller body regions **618D**. As indicated earlier, these thermal cycles also cause N+ epi **602** to diffuse upward as depicted in FIG. 6E. It is important to ensure that upon completion of the manufacturing process, the two body regions between every two adjacent trenches remain spaced apart and do not merge, otherwise the Schottky diode is eliminated. Another goal in designing the process is to ensure that N- epi **620** and body region **618D** after completion of the process have substantially the same depth, although slightly different depths would not be fatal to the operation of the device. These goals can be achieved by adjusting a number of the process steps and parameters including the thermal cycles, the depth of the first trench recess (FIG. 6B), and doping concentration of various regions including the body regions, the N- epi region and the N+ epi region.

In FIG. 6F, without using a mask in the active region, a dimple etch process is performed to etch through N+ regions **622A** such that outer portions **622B** of N+ regions **622A** are preserved. The preserved outer portions **622A** form the source region. A dimple **624** is thus formed between every two adjacent trench. Dimples **624** form contact openings extending below source regions **622B** and into N- regions **620**. "Dimple etch" as used in this disclosure refers to silicon etch techniques which result in formation of silicon regions with sloped, rounded outer profiles as do source regions **622B** in FIG. 6F. In one embodiment, the dimples extend to a depth within the bottom half of body regions **618D**. As indicated before, a deeper dimple results in formation of a Schottky contact below the source regions. This helps divert reverse avalanche current away from the source, thus preventing the parasitic bipolar transistor from turning on. While the above dimple etch does not require a mask in the active region, in an alternate embodiment a mask is used to define a central portion of N+ regions **622A** that is etched through to the desired depth. Outer portions of N+ regions **622A** extending under such a mask are thus preserved. These outer regions form the source regions.

Using a masking layer, P-type dopants are implanted into the dimple region intermittently along each stripe. Islands of heavy body regions (not shown) are thus formed between every two adjacent trench. If the heavy body implementation of FIG. 4 is desired, a high enough dosage of P-type dopants need to be used during the heavy body implant in order to counter-dope those portions of the source regions where the heavy body regions are to be formed. If the heavy body implementation of FIG. 5 is desired, a lower dosage of P-type dopants needs to be used during the implant so that the source regions are not counter-doped and thus remain intact.

In FIG. 6F, conventional techniques can be used to form a Schottky barrier metal **630** over the structure. Schottky barrier metal **630** fills dimples **624**, and where metal **630** comes in electrical contact with N- regions **620**, a Schottky diode is formed. Metal layer **630** also contacts source regions **622B** and the heavy body regions.

In the process sequence depicted by FIGS. 6A-6F, neither of the two masks used requires critical alignment. As a result, the integrated MOSFET-Schottky structure has many vertical

and horizontal self-aligned features. In addition, the above-described process embodiments enable reduction of the channel length. Conventional processes utilize an implant and drive technique to form the body regions. This technique results in a tapered doping profile in the channel region requiring a longer channel length. In contrast, the above-described alternate techniques of selective epitaxial growth and two-pass angled implant for forming the body regions provide a uniform doping profile in the channel region, thus allowing a shorter channel length to be used. The on-resistance of the device is thus improved.

Moreover, use of a double epi structure provides design flexibility enabling optimization of the breakdown voltage and the on resistance while maintaining tight control over the MOSFET threshold voltage (V_{th}). Tight control over V_{th} is achieved by forming body regions **618** in N- epi **618** which compared to N+ epi **602** exhibits a far more consistent and predictable doping concentration. Forming body regions in a background region with a predictable doping concentration allows tighter control over the threshold voltage. On the other hand, shielded electrodes **605** extending into N+ epi **602** allows use of a higher doping concentration in N+ epi **602** for the same breakdown voltage. A lower on-resistance is thus obtained for the same breakdown voltage and without adversely impacting control over the MOSFET threshold voltage.

FIGS. 7A-7C show simulated avalanche current flow lines for three different dimple depths in an integrated trench MOSFET-Schottky diode structure. In the FIG. 7A structure, dimple **729A** extends to a depth just below source region **722**. In the FIG. 7B structure, dimple **729B** extends deeper to about one half the height of body region **718**. In the FIG. 7C structure, dimple **729C** extends even deeper to just above the bottom of body region **718**. In FIGS. 7A-7C, a gap appears in the top metal **730**. This gap was included only for simulation purposes, and in practice, no such gap would be present in the top metal as is evident from the other figures in this disclosure.

As can be seen in FIG. 7A, avalanche current flow lines **732A** are in close proximity to source region **722**. However, as the dimple depth is increased in FIG. 7B and yet deeper in FIG. 7C, avalanche current flow lines **732B** and **732C** are shifted further away from source region **722** toward the Schottky region. The diversion of avalanche current away from the source region helps prevent the parasitic bipolar transistor from turning on, and thus improves the ruggedness of the device. In essence, the Schottky region acts like a heavy body region in collecting the avalanche current, thus eliminating the need for heavy body region for this purpose. Heavy body regions would still be required to obtain a good contact to the body region, but the frequency and size of the heavy body regions can be significantly reduced compared to conventional MOSFET structures. This frees up a large silicon area which is allocated to the Schottky diode. Thus, for the exemplary simulated structures in FIGS. 7A-7C, dimples which extend to a depth within the bottom half of body region **718** provide optimum results.

While the invention has been described using shielded gate trench MOSFET embodiments, implementation of the invention in other shielded gate MOSFET structures and trench gate MOSFETs with thick bottom dielectric as well as other types of power devices would be obvious to one skilled in this art in view of this disclosure. For example, the above-described techniques for integrating Schottky diode with MOSFET can be similarly implemented in the various power devices disclosed in the above-referenced U.S. patent application Ser. No. 11/026,276, filed Dec. 29, 2004, in particular

in the trench gate, shielded gate, and charge balance devices shown, for example, in FIGS. 1, 2A, 3A, 3B, 4A, 4C, 5C, 9B, 9C, 10-12, and 24.

Although a number of specific embodiments are shown and described above, embodiments of the invention are not limited thereto. For example, while some embodiments of the invention are described using the open cell structure, implementing the invention using closed cell structures with various geometric shapes such as polygonal, circular, and rectangular, would be obvious to one skilled in this art in view of this disclosure. Further, while the embodiments of the invention are described using n-channel devices, the conductivity type of the silicon regions in these embodiments can be reversed to obtain p-channel devices. Therefore, the scope of the present invention should be determined not with reference to the above description but should, instead, be determined with reference to the appended claim, along with their full scope of equivalents.

What is claimed is:

1. A structure comprising:
 - a monolithically integrated trench FET and Schottky diode, the monolithically integrated trench FET and Schottky diode comprising:
 - a pair of trenches terminating in a first silicon region of first conductivity type;
 - two body regions of a second conductivity type between the pair of trenches, the two body regions being separated by a second silicon region of the first conductivity type;
 - a source region of the first conductivity type over each body region;
 - a contact opening extending between the pair of trenches to a depth below the source regions; and
 - an interconnect layer filling the contact opening so as to electrically contact the source regions and the second silicon region, the interconnect layer forming a Schottky contact with the second silicon region.
 2. The structure of claim 1 wherein the first silicon region has a higher doping concentration than the second silicon region.
 3. The structure of claim 1 wherein each body region vertically extends between a corresponding source region and the first silicon region, and the interconnect layer electrically contacts the second silicon region at a depth along the bottom half of the body regions.
 4. The structure of claim 1 wherein each of the two body regions has a substantially uniform doping concentration.
 5. The structure of claim 1 wherein the first silicon region is a first epitaxial layer, and the second silicon region is a second epitaxial layer, the first epitaxial layer extending over a substrate of the first conductivity type, the substrate having a higher doping concentration than the first epitaxial layer, and the first epitaxial layer having a higher doping concentration than the second epitaxial layer.
 6. The structure of claim 1 wherein the two body regions and the corresponding source regions are self-aligned to the pair of trenches.
 7. The structure for claim 1 further comprising a heavy body region of the second conductivity type formed between the pair of trenches such that the heavy body region electrically contacts each of the two body regions and the second silicon region, the heavy body region having a higher doping concentration than the two body regions.
 8. The structure of claim 7 wherein the two body regions, the source regions, and the heavy body region are self-aligned to the pair of trenches.

9. The structure of claim 1 wherein the two body regions and the second silicon region have substantially the same depth.

10. The structure of claim 1 further comprising:
 - a recessed gate electrode in each trench; and
 - a dielectric cap insulating each gate electrode from the interconnect layer.
11. The structure of claim 10 further comprising:
 - a shield electrode in each trench below the recessed gate electrode; and
 - a shield dielectric insulating the shield electrode from the first silicon region.
12. The structure of claim 10 further comprising:
 - a thick bottom dielectric extending along a bottom of each trench directly beneath the recessed gate electrode.
13. The structure of claim 1 further comprising a DC to DC synchronous buck converter in which the monolithically integrated trench FET and Schottky diode is coupled to a load as a low-side switch.
14. The structure of claim 1 wherein the interconnect layer is a Schottky barrier metal layer.
15. The structure of claim 1 wherein each of the two body regions forms a pn junction with the second silicon region.
16. The structure of claim 1 wherein the Schottky contact is formed at a depth below the source regions.
17. A structure comprising a monolithically integrated trench MOSFET and Schottky diode, the monolithically integrated trench MOSFET and Schottky diode comprising:
 - a first epitaxial layer of a first conductivity type;
 - a second epitaxial layer of the first conductivity type over the first epitaxial layer, the first epitaxial layer having a higher doping concentration than the second epitaxial layer;
 - a plurality of trenches extending through the second epitaxial layer and terminating in the first epitaxial layer;
 - two body regions of a second conductivity type between every two adjacent trenches, the two body regions being separated by a portion of the second epitaxial layer;
 - a source region of the first conductivity type over each body region;
 - a contact opening extending between every two adjacent trenches to a depth below the source regions; and
 - a Schottky barrier metal layer filling the contact openings so as to electrically contact the source region and the portion of the second epitaxial layer, the Schottky barrier metal layer forming a Schottky contact with the portion of the second epitaxial layer.
18. The structure of claim 17 wherein each body region vertically extends between a corresponding source region and the first epitaxial layer, and the Schottky barrier metal layer electrically contacts the portion of the second epitaxial layer at a depth along the bottom half of the body regions.
19. The structure of claim 17 wherein each of the two body regions has a substantially uniform doping concentration.
20. The structure of claim 17 wherein the first epitaxial layer extends over a substrate of the first conductivity type, the substrate having a higher doping concentration than the first epitaxial layer.
21. The structure of claim 17 wherein the two body regions and the corresponding source regions are self-aligned to the two adjacent trenches between which they are located.
22. The structure for claim 17 further comprising a plurality of heavy body regions of the second conductivity type formed between every two adjacent trenches such that each

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heavy body region electrically contacts the two body regions and the portion of the second epitaxial layer located between the two adjacent trenches.

23. The structure of claim 22 wherein the two body regions, the corresponding source regions, and the plurality of heavy body regions are self-aligned to the two adjacent trenches between which they are located.

24. The structure of claim 17 wherein the two body regions and the second epitaxial layer have substantially the same depth.

25. The structure of claim 17 further comprising:
a recessed gate electrode in each trench; and
a dielectric cap insulating each gate electrode from the Schottky barrier metal layer.

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26. The structure of claim 25 further comprising:
a shield electrode in each trench below the recessed gate electrode; and
a shield dielectric insulating the shield electrode from the first epitaxial layer.

27. The structure of claim 25 further comprising:
a thick bottom dielectric extending along the bottom of each trench directly beneath the recessed gate electrode.

28. The structure of claim 17 further comprising a DC to DC synchronous buck converter in which the monolithically integrated trench MOSFET and Schottky diode is coupled to a load as a low-side switch.

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